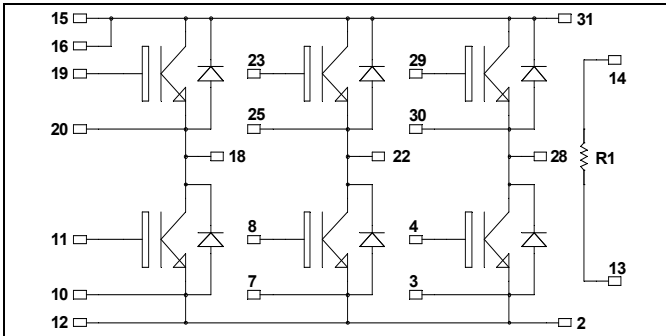
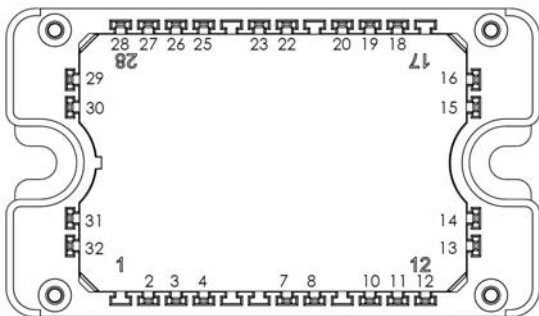


**3 Phase bridge
Trench + Field Stop IGBT3
Power Module**

**$V_{CES} = 600V$
 $I_C = 50A^* @ T_c = 80^\circ C$**



It is recommended to connect a decoupling capacitor between pins 31 & 2 to reduce switching overvoltages, if DC Power is connected between pins 15, 16 & 12. Pins 15 & 16 must be shorted together.



Application

- Motor control

Features

- Trench + Field Stop IGBT3 Technology
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 20 kHz
 - Low leakage current
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
- Internal thermistor for temperature monitoring

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS compliant

All ratings @ $T_j = 25^\circ C$ unless otherwise specified

Absolute maximum ratings (Per IGBT)

Symbol	Parameter	Max ratings	Unit
V_{CES}	Collector - Emitter Voltage	600	V
I_C	Continuous Collector Current	$T_C = 25^\circ C$	80*
		$T_C = 80^\circ C$	50*
I_{CM}	Pulsed Collector Current	$T_C = 25^\circ C$	100
V_{GE}	Gate – Emitter Voltage	± 20	V
P_D	Power Dissipation	$T_C = 25^\circ C$	176
RBSOA	Reverse Bias Safe Operating Area	$T_J = 150^\circ C$	100A @ 550V

* Specification of IGBT device but output current must be limited due to size of output pin

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

Electrical Characteristics (Per IGBT)

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit	
I _{CES}	Zero Gate Voltage Collector Current	V _{GE} = 0V, V _{CE} = 600V			250	μA	
V _{CE(sat)}	Collector Emitter Saturation Voltage	V _{GE} = 15V I _C = 50A		T _j = 25°C	1.5	1.9	V
				T _j = 150°C		1.7	
V _{GE(th)}	Gate Threshold Voltage	V _{GE} = V _{CE} , I _C = 600μA	5.0	5.8	6.5	V	
I _{GES}	Gate – Emitter Leakage Current	V _{GE} = 20V, V _{CE} = 0V			600	nA	

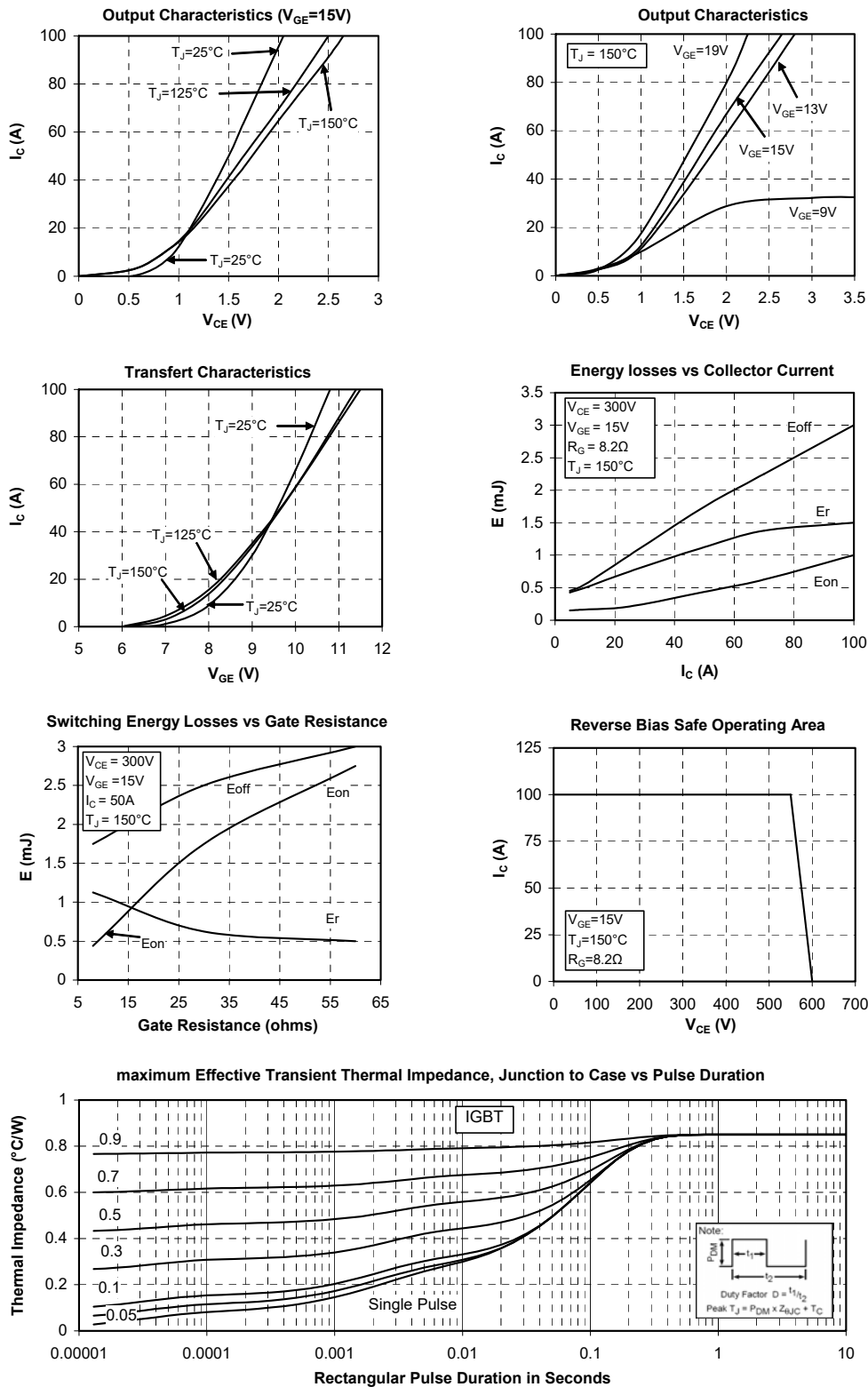
Dynamic Characteristics (Per IGBT)

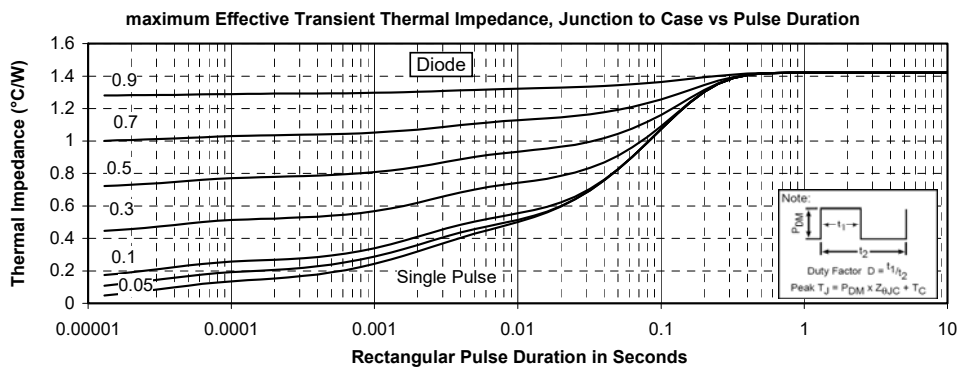
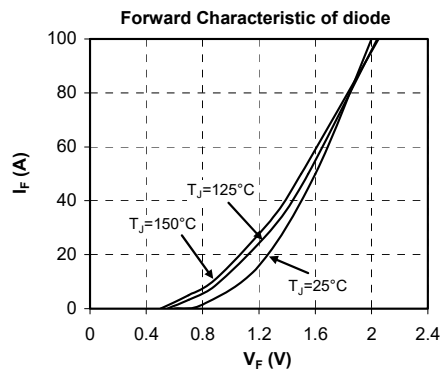
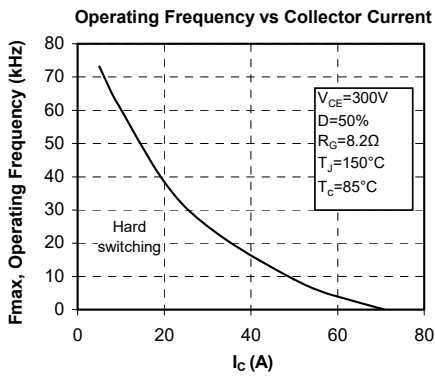
Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C _{ies}	Input Capacitance	V _{GE} = 0V V _{CE} = 25V f = 1MHz		3150		pF
C _{oes}	Output Capacitance			200		
C _{res}	Reverse Transfer Capacitance			95		
T _{d(on)}	Turn-on Delay Time	Inductive Switching (25°C) V _{GE} = ±15V V _{Bus} = 300V I _C = 50A R _G = 8.2Ω		110		ns
T _r	Rise Time			45		
T _{d(off)}	Turn-off Delay Time			200		
T _f	Fall Time			40		
T _{d(on)}	Turn-on Delay Time	Inductive Switching (150°C) V _{GE} = ±15V V _{Bus} = 300V I _C = 50A R _G = 8.2Ω		120		ns
T _r	Rise Time			50		
T _{d(off)}	Turn-off Delay Time			250		
T _f	Fall Time			60		
E _{on}	Turn-on Switching Energy	V _{GE} = ±15V V _{Bus} = 300V I _C = 50A R _G = 8.2Ω	T _j = 150°C		0.43	mJ
E _{off}	Turn-off Switching Energy			T _j = 150°C		1.75
R _{thJC}	Junction to Case Thermal Resistance				0.85	°C/W

Reverse diode ratings and characteristics (Per diode)

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V _{RRM}	Peak Repetitive Reverse Voltage				600	V
I _{RM}	Reverse Leakage Current	V _R = 600V			250	μA
I _F	DC Forward Current	T _c = 80°C		50		A
V _F	Diode Forward Voltage	I _F = 50A V _{GE} = 0V	T _j = 25°C	1.6	2	V
			T _j = 150°C		1.5	
t _{rr}	Reverse Recovery Time	I _F = 50A V _R = 300V di/dt = 1800A/μs	T _j = 25°C	100		ns
			T _j = 150°C		150	
Q _{rr}	Reverse Recovery Charge		T _j = 25°C	2.6		μC
			T _j = 150°C		5.4	
E _r	Reverse Recovery Energy		T _j = 25°C	0.6		mJ
			T _j = 150°C		1.2	
R _{thJC}	Junction to Case Thermal Resistance				1.42	°C/W

Typical Performance Curve





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